

## N-Channel 150 V (D-S) 175 °C MOSFET

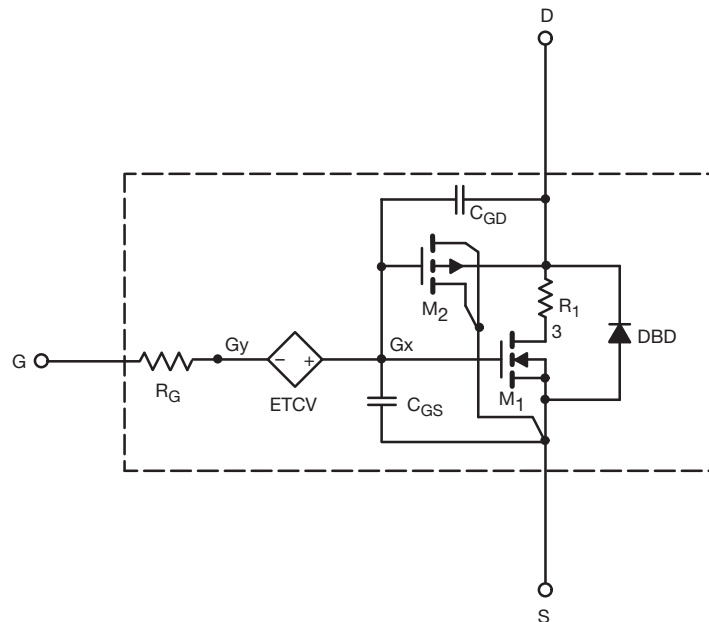
### DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

### SUBCIRCUIT MODEL SCHEMATIC



### Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

# SPICE Device Model SQM85N15-19



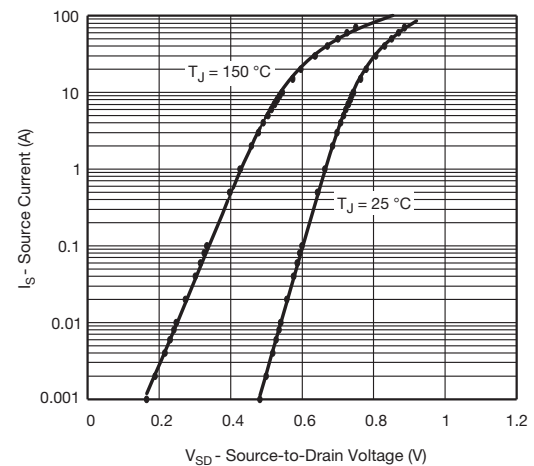
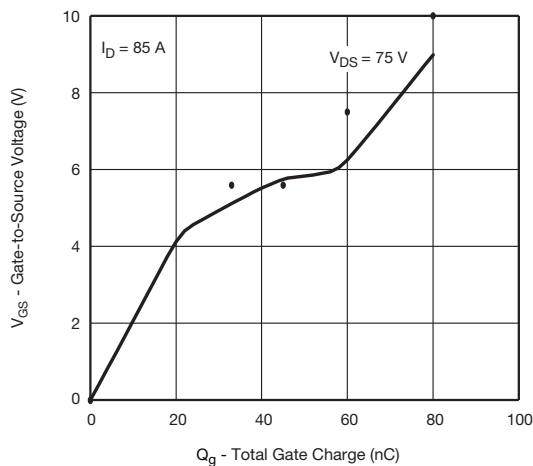
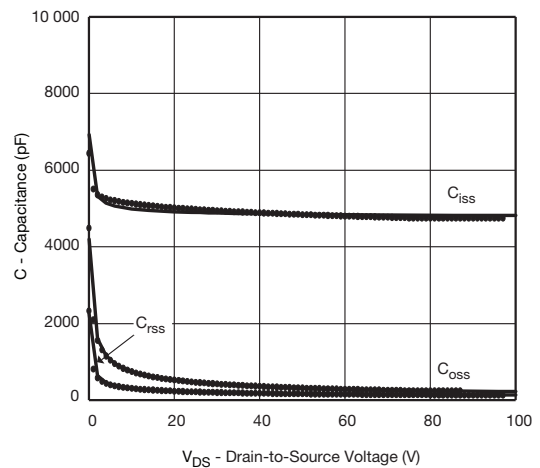
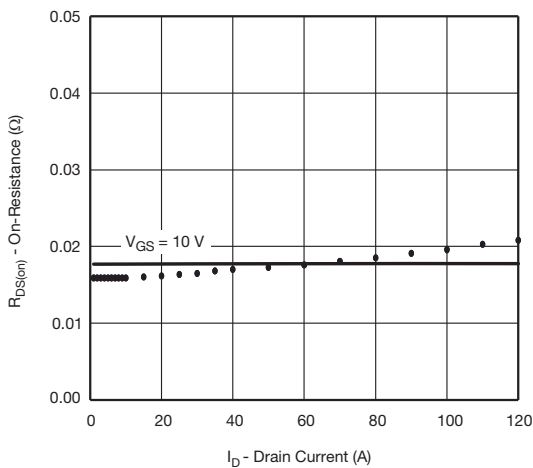
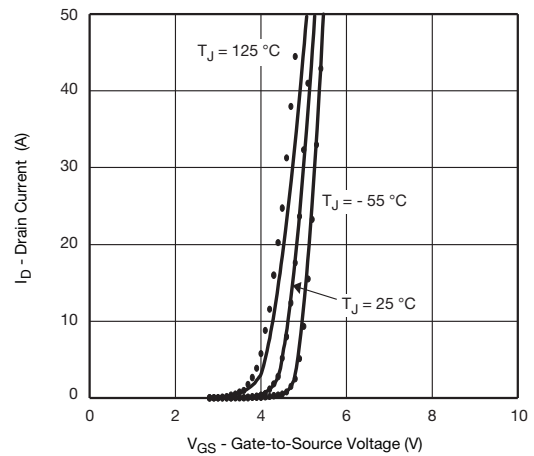
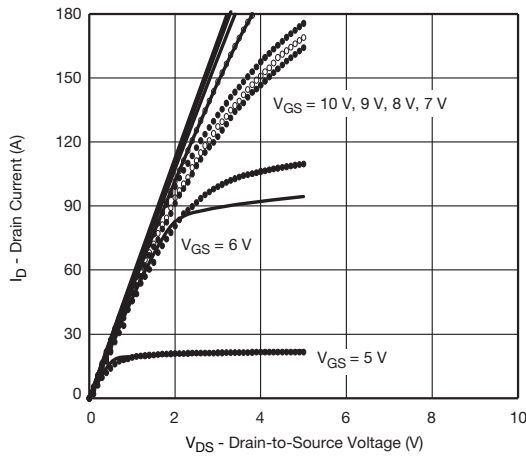
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| SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted) |              |   |                |               |          |
|---|--------------|---|----------------|---------------|----------|
| PARAMETER   | SYMBOL       | TEST CONDITIONS   | SIMULATED DATA | MEASURED DATA | UNIT     |
| <b>Static</b>   |              |   |                |               |          |
| Gate-Source Threshold Voltage   | $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$                    | 2.4            | -             | V        |
| Drain-Source On-State Resistance <sup>a</sup>                               | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ , $I_D = 30\text{ A}$                          | 0.017          | 0.016         | $\Omega$ |
| Forward Transconductance <sup>a</sup>                                       | $g_{fs}$     | $V_{DS} = 15\text{ V}$ , $I_D = 30\text{ A}$                          | 62             | 79            | S        |
| Body Diode Voltage  | $V_{SD}$     | $I_S = 85\text{ A}$   | 0.92           | 0.90          | V        |
| <b>Dynamic<sup>b</sup></b>  |              |   |                |               |          |
| Input Capacitance   | $C_{iss}$    | $V_{DS} = 25\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$   | 4900           | 5026          | pF       |
| Output Capacitance  | $C_{oss}$    |   | 450            | 450           |          |
| Reverse Transfer Capacitance  | $C_{rss}$    |   | 207            | 165           |          |
| Total Gate Charge   | $Q_g$        | $V_{DS} = 75\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 85\text{ A}$ | 84             | 80            | nC       |
| Gate-Source Charge  | $Q_{gs}$     |   | 33             | 33            |          |
| Gate-Drain Charge   | $Q_{gd}$     |   | 12             | 12            |          |

## Notes

- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.

## COMPARISON OF MODEL WITH MEASURED DATA ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



### Note

- Dots and squares represent measured data.



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